PM200CLA120

FLAT-BASE TYPE
INSULATED PACKAGE

PM200CLA120

FEATURE

a) Adopting new 5th generation IGBT (CSTBT) chip, which performance is improved by 1µm fine rule process.
For example, typical V_{CE}(sat)=1.9V @Tj=125°C

b) I adopt the over-temperature conservation by Tj detection of CSTBT chip, and error output is possible from all each conservation upper and lower arm of IPM.

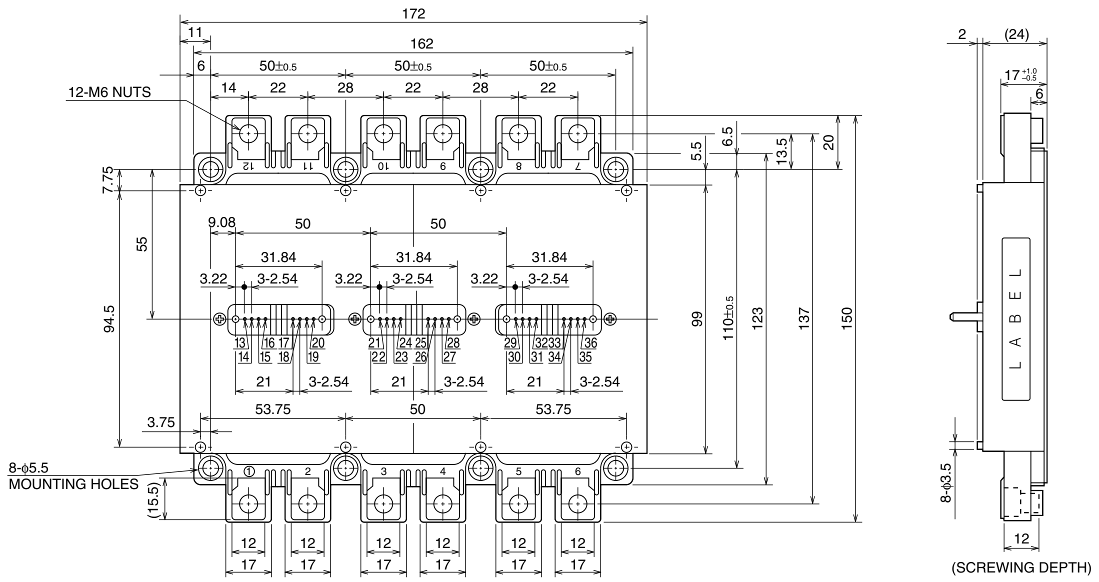
- 3φ 200A, 1200V Current-sense IGBT type inverter
- Monolithic gate drive & protection logic
- Detection, protection & status indication circuits for, short-circuit, over-temperature & under-voltage (Fo available from all arm devices)
- Acoustic noise-less 37kW class inverter application
- UL Recognized Yellow Card No.E80276(N)
File No.E80271

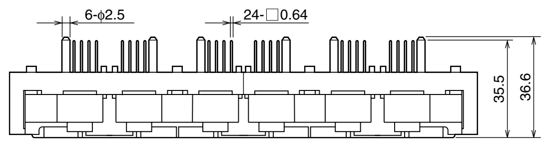
APPLICATION

General purpose inverter, servo drives and other motor controls

PACKAGE OUTLINES

Dimensions in mm



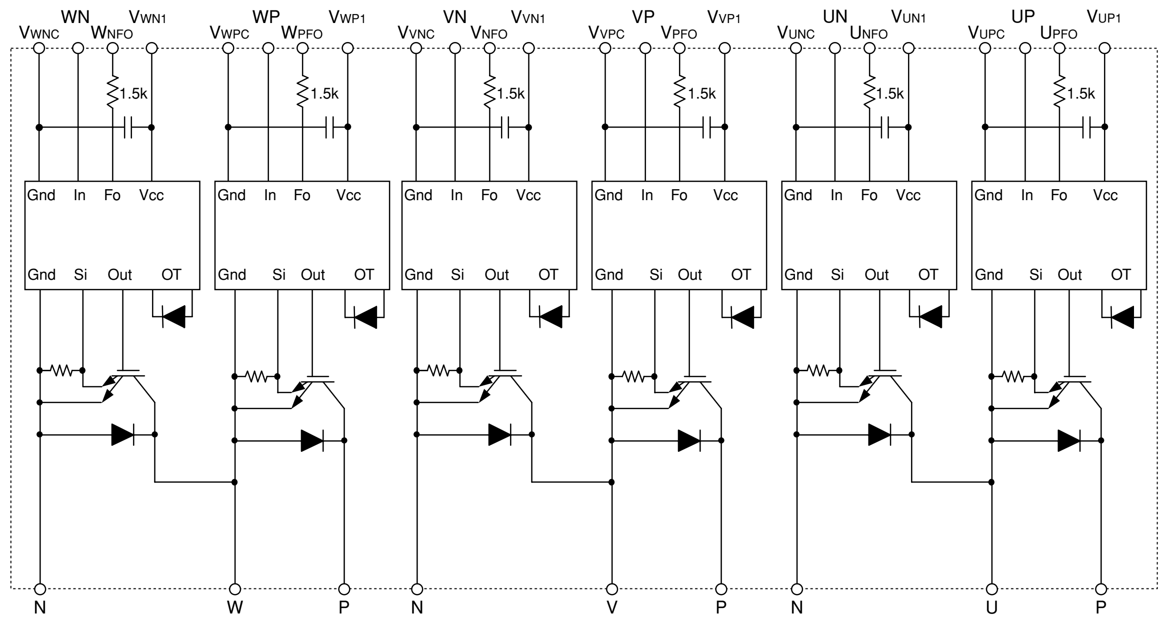


Terminal code

1. N	7. W	13. VUPC	19. UN	25. VVNC	31. WP
2. P	8. W	14. UPFO	20. VUN1	26. VNFO	32. VWP1
3. N	9. V	15. UP	21. VVPC	27. VN	33. VWNC
4. P	10. V	16. VUP1	22. VPFO	28. VVN1	34. WNFO
5. N	11. U	17. VUNC	23. VP	29. VWPC	35. WN
6. P	12. U	18. UNFO	24. VVP1	30. WPFO	36. VWN1

Jul. 2005

INTERNAL FUNCTIONS BLOCK DIAGRAM



MAXIMUM RATINGS (T_j = 25°C, unless otherwise noted)

INVERTER PART

Symbol	Parameter	Condition	Ratings	Unit
V_{CES}	Collector-Emitter Voltage	V_D = 15V, V_{CIN} = 15V	1200	V
$\pm I_C$	Collector Current	T_C = 25°C	200	A
$\pm I_{CP}$	Collector Current (Peak)	T_C = 25°C	400	A
P_C	Collector Dissipation	T_C = 25°C (Note-1)	1041	W
T_j	Junction Temperature		–20 ~ +150	°C

CONTROL PART

Symbol	Parameter	Condition	Ratings	Unit
V_D	Supply Voltage	Applied between : V_{UP1}-V_{UPC}, V_{VP1}-V_{VPC}, V_{WP1}-V_{WPC} V_{UN1}-V_{UNC}, V_{VN1}-V_{VNC}, V_{WN1}-V_{WNC}	20	V
V_{CIN}	Input Voltage	Applied between : U_P-V_{UPC}, V_P-V_{VPC}, W_P-V_{WPC} U_N-V_{UNC}, V_N-V_{VNC}, W_N-V_{WNC}	20	V
V_{FO}	Fault Output Supply Voltage	Applied between : U_{PFO}-V_{UPC}, V_{PFO}-V_{VPC}, W_{PFO}-V_{WPC} U_{NFO}-V_{UNC}, V_{NFO}-V_{VNC}, W_{NFO}-V_{WNC}	20	V
I_{FO}	Fault Output Current	Sink current at U_{PFO}, V_{PFO}, W_{PFO}, U_{NFO}, V_{NFO}, W_{NFO} terminals	20	mA

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TOTAL SYSTEM

Symbol	Parameter	Condition	Ratings	Unit
$V_{CC(PROT)}$	Supply Voltage Protected by SC	V_D = 13.5 ~ 16.5V, Inverter Part, T_j = +125°C Start	800	V
$V_{CC(surge)}$	Supply Voltage (Surge)	Applied between : P-N, Surge value	1000	V
T_{stg}	Storage Temperature		–40 ~ +125	°C
V_{iso}	Isolation Voltage	60Hz, Sinusoidal, Charged part to Base, AC 1 min.	2500	V_{rms}

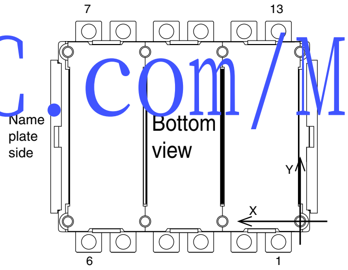
THERMAL RESISTANCES

Symbol	Parameter	Condition	Limits Min.	Limits Typ.	Limits Max.	Unit
$R_{th(j-c)Q}$	Junction to case Thermal Resistances	Inverter IGBT (per 1 element) (Note-1)	—	—	0.12	°C/W
$R_{th(j-c)F}$		Inverter FWDi (per 1 element) (Note-1)	—	—	0.20	
$R_{th(c-f)}$	Contact Thermal Resistance	Case to fin, (per 1 module) Thermal grease applied (Note-1)	—	—	0.014	

(Note-1) Tc measurement point is just under the chip.
If you use this value, $R_{th(f-a)}$ should be measured just under the chips.

Table 1: Tc (under the chip) measurement point is below. (Unit : mm)

arm / axis	UP IGBT	UP FWDi	VP IGBT	VP FWDi	WP IGBT	WP FWDi	UN IGBT	UN FWDi	VN IGBT	VN FWDi	WN IGBT	WN FWDi
X	26.5	23.6	76.5	73.6	126.5	123.6	23.4	26.4	73.4	76.4	123.4	126.4
Y	85.5	70.5	85.5	70.5	85.5	70.5	24.5	39.5	24.5	39.5	24.5	39.5



ELECTRICAL CHARACTERISTICS (Tj = 25°C, unless otherwise noted)
INVERTER PART

Symbol	Parameter	Condition		Limits Min.	Limits Typ.	Limits Max.	Unit
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	V_D = 15V, I_C = 200A, V_{CIN} = 0V (Fig. 1)	T_j = 25°C	—	1.8	2.3	V
			T_j = 125°C	—	1.9	2.4	
V_{EC}	FWDi Forward Voltage	$-I_C$ = 200A, V_D = 15V, V_{CIN} = 15V (Fig. 2)		—	2.8	3.9	V
t_{on}	Switching Time	V_D = 15V, V_{CIN} = 0V↔15V, V_{CC} = 600V, I_C = 200A, T_j = 125°C, Inductive Load (Fig. 3, 4)		0.5	1.0	2.5	µs
t_{rr}				—	0.5	0.8	
$t_{c(on)}$				—	0.4	1.0	
t_{off}				—	2.3	3.5	
$t_{c(off)}$				—	0.7	1.2	
I_{CES}	Collector-Emitter Cutoff Current	V_{CE} = V_{CES}, V_{CIN} = 15V (Fig. 5)	T_j = 25°C	—	—	1	mA
			T_j = 125°C	—	—	10	

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CONTROL PART

Symbol	Parameter	Condition		Limits			Unit
				Min.	Typ.	Max.	
I_D	Circuit Current	V_D = 15V, V_{CIN} = 15V	V_{*N1}-V_{*NC}	—	11	18	mA
			V_{*P1}-V_{*PC}	—	11	18	
$V_{th(ON)}$	Input ON Threshold Voltage	Applied between : U_P-V_{UPC}, V_P-V_{VPC}, W_P-V_{WPC}		1.2	1.5	1.8	V
$V_{th(OFF)}$	Input OFF Threshold Voltage	U_N-V_{UNC}, V_N-V_{VNC}, W_N-V_{WNC}		1.7	2.0	2.3	
SC	Short Circuit Trip Level	$-20 \le T_j \le 125°C$, V_D = 15V (Fig. 3,6)		400	—	—	A
$t_{off(SC)}$	Short Circuit Current Delay Time	V_D = 15V (Fig. 3,6)		—	0.2	—	µs
OT	Over Temperature Protection	V_D = 15V	Trip level	135	145	—	°C
OT_r		Detect T_j of IGBT chip	Reset level	—	125	—	
UV	Supply Circuit Under-Voltage Protection	$-20 \le T_j \le 125°C$	Trip level	11.5	12.0	12.5	V
UV_r			Reset level	—	12.5	—	
$I_{FO(H)}$	Fault Output Current	V_D = 15V, V_{FO} = 15V (Note-2)		—	—	0.01	mA
$I_{FO(L)}$				—	10	15	
t_{FO}	Minimum Fault Output Pulse Width	V_D = 15V (Note-2)		1.0	1.8	—	ms

(Note-2) Fault output is given only when the internal SC, OT & UV protections schemes of either upper or lower arm device operate to protect it.

MECHANICAL RATINGS AND CHARACTERISTICS

Symbol	Parameter	Condition	Limits			Unit
			Min.	Typ.	Max.	
—	Mounting torque	Main terminal screw : M6	3.5	4.5	4.5	N • m
—	Mounting torque	Mounting part screw : M5	2.5	3.0	3.5	N • m
—	Weight	—	—	1250	—	g

RECOMMENDED CONDITIONS FOR USE

Symbol	Parameter	Condition	Recommended value	Unit
V_{CC}	Supply Voltage	Applied across P-N terminals	≤ 800	V
V_D	Control Supply Voltage	Applied between : V_{UP1}-V_{UPC}, V_{VP1}-V_{VPC}, V_{WP1}-V_{WPC} V_{UN1}-V_{UNC}, V_{VN1}-V_{VNC}, V_{WN1}-V_{WNC} (Note-3)	15 ± 1.5	V
$V_{CIN(ON)}$	Input ON Voltage	Applied between : U_P-V_{UPC}, V_P-V_{VPC}, W_P-V_{WPC}	≤ 0.8	V
$V_{CIN(OFF)}$	Input OFF Voltage	U_N-V_{UNC}, V_N-V_{VNC}, W_N-V_{WNC}	≥ 9.0	
f_{PWM}	PWM Input Frequency	Using Application Circuit of Fig. 8	≤ 20	kHz
t_{dead}	Arm Shoot-through Blocking Time	For IPM's each input signals (Fig. 7)	≥ 3.0	µs

(Note-3) With ripple satisfying the following conditions: dv/dt swing ≤ ±5V/µs, Variation ≤ 2V peak to peak

PRECAUTIONS FOR TESTING

1. Before appling any control supply voltage (V_D), the input terminals should be pulled up by resistores, etc. to their corresponding supply voltage and each input signal should be kept off state.
   After this, the specified ON and OFF level setting for each input signal should be done.
2. When performing "SC" tests, the turn-off surge voltage spike at the corresponding protection operation should not be allowed to rise above V_{CES} rating of the device.
   (These test should not be done by using a curve tracer or its equivalent.)

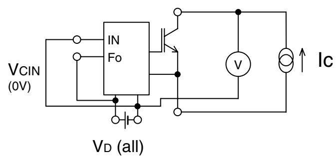


Fig. 1 $V_{CE(sat)}$ Test

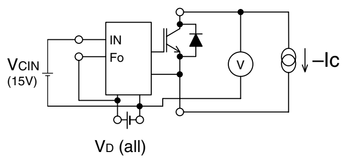


Fig. 2 V_{EC} Test

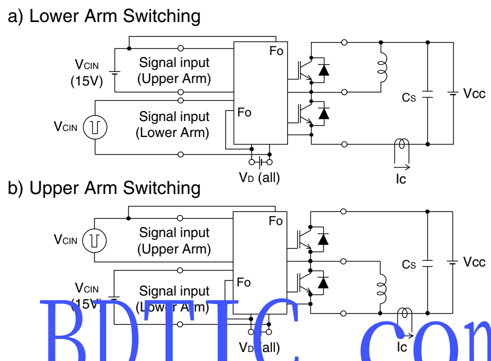


Fig. 3 Switching time and SC test circuit

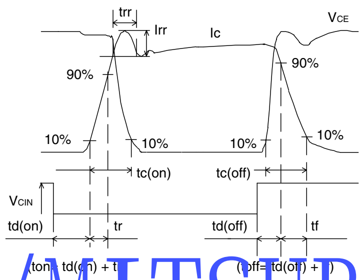


Fig. 4 Switching time test waveform

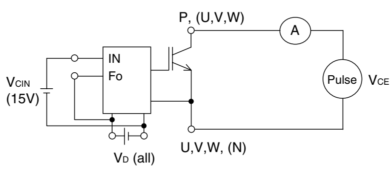


Fig. 5 I_{CES} Test

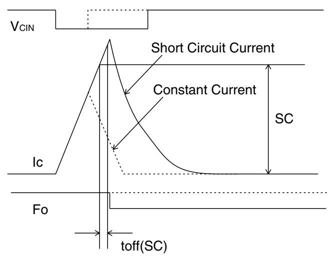
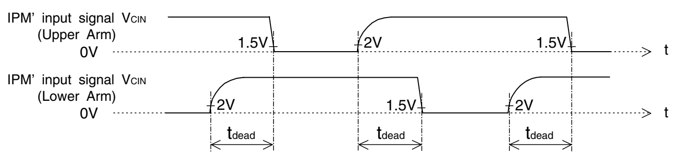


Fig. 6 SC test waveform



1.5V: Input on threshold voltage Vth(on) typical value, 2V: Input off threshold voltage Vth(off) typical value

Fig. 7 Dead time measurement point example

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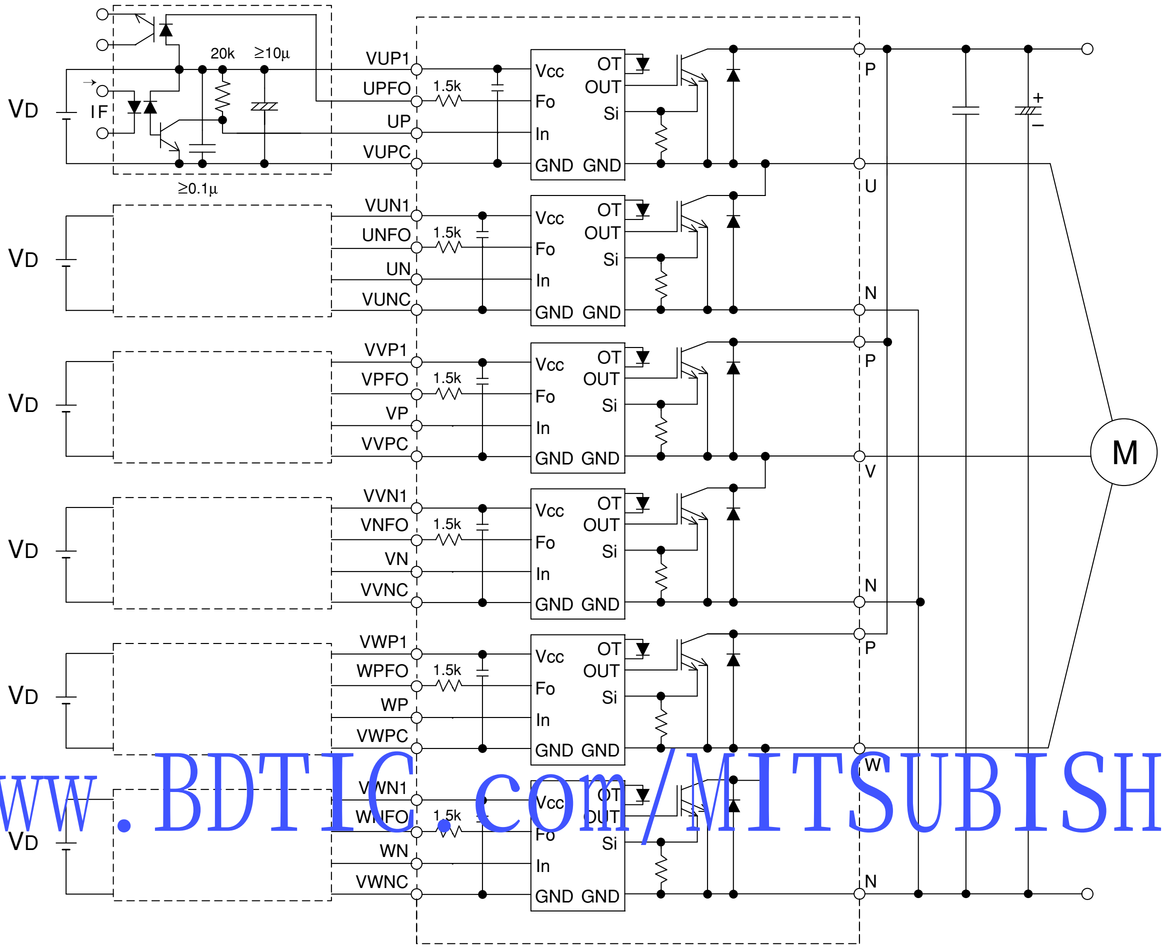


: Interface which is the same as the U-phase

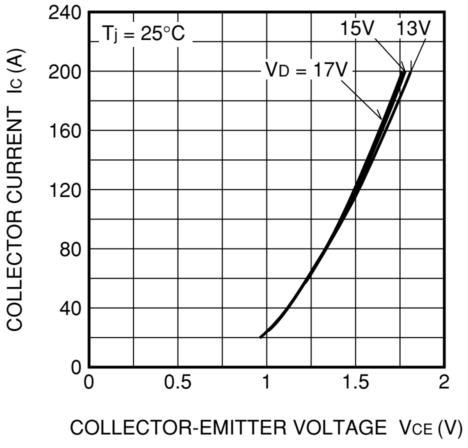
Fig. 8 Application Example Circuit

NOTES FOR STABLE AND SAFE OPERATION ;

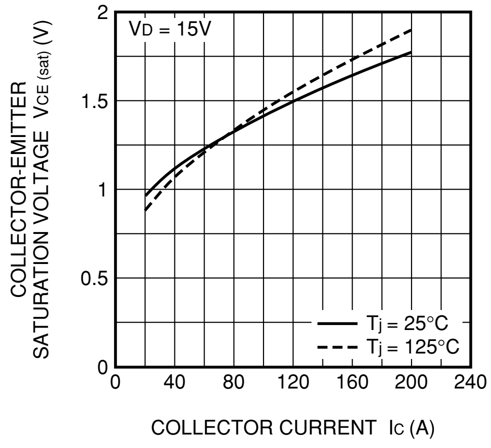
- Design the PCB pattern to minimize wiring length between opto-coupler and IPM's input terminal, and also to minimize the stray capacity between the input and output wirings of opto-coupler.
- Connect low impedance capacitor between the Vcc and GND terminal of each fast switching opto-coupler.
- Fast switching opto-couplers: t_{PLH}, $t_{PHL} \leq 0.8\mu s$, Use High CMR type.
- Slow switching opto-coupler: CTR > 100%
- Use 6 isolated control power supplies (V_D). Also, care should be taken to minimize the instantaneous voltage charge of the power supply.
- Make inductance of DC bus line as small as possible, and minimize surge voltage using snubber capacitor between P and N terminal.
- Use line noise filter capacitor (ex. 4.7nF) between each input AC line and ground to reject common-mode noise from AC line and improve noise immunity of the system.

PERFORMANCE CURVES

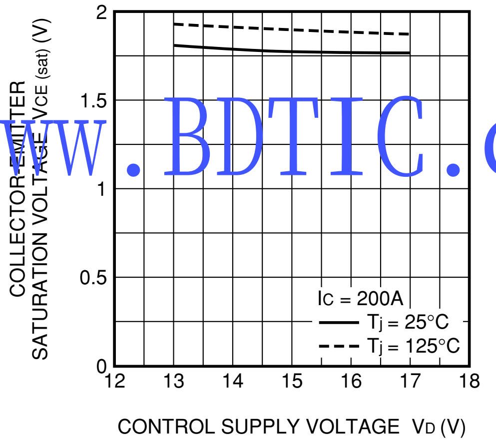
OUTPUT CHARACTERISTICS (TYPICAL)



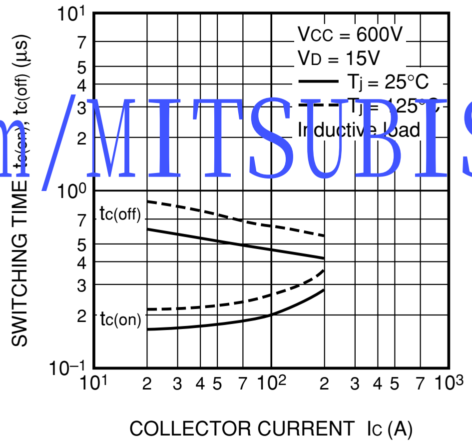
COLLECTOR-EMITTER SATURATION VOLTAGE (VS. IC) CHARACTERISTICS (TYPICAL)



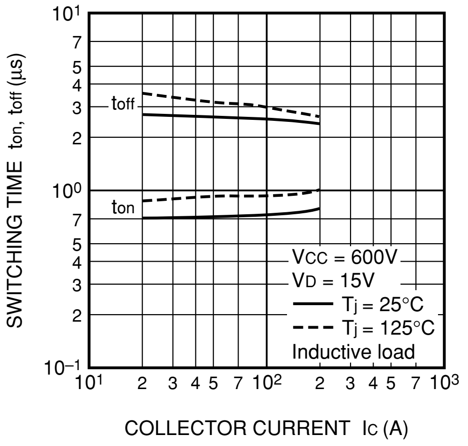
COLLECTOR-EMITTER SATURATION VOLTAGE (VS. VD) CHARACTERISTICS (TYPICAL)



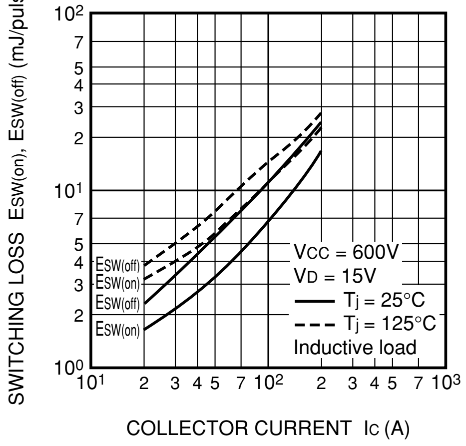
SWITCHING TIME CHARACTERISTICS (TYPICAL)



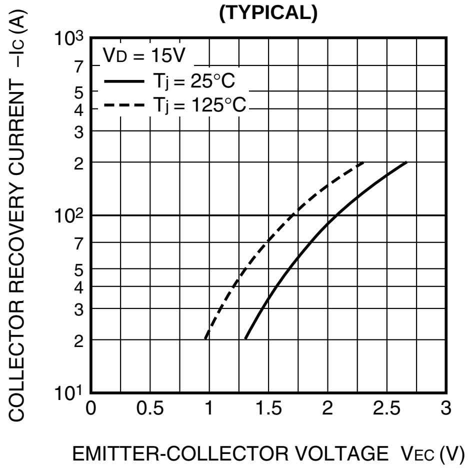
SWITCHING TIME CHARACTERISTICS (TYPICAL)



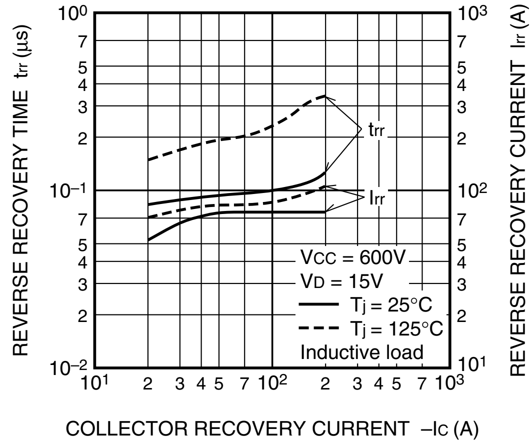
SWITCHING LOSS CHARACTERISTICS (TYPICAL)



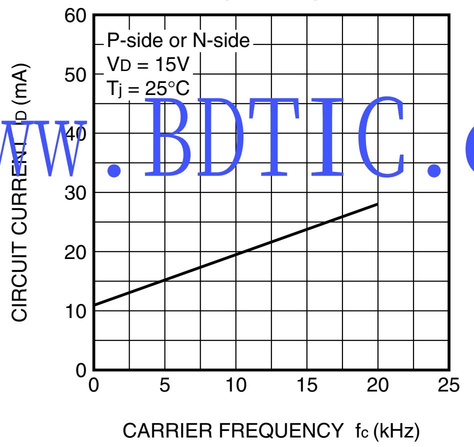
DIODE FORWARD CHARACTERISTICS (TYPICAL)



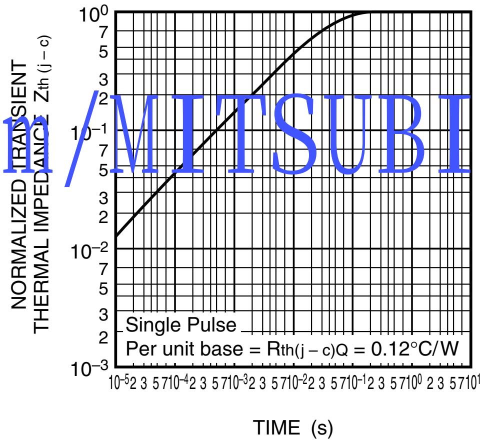
DIODE REVERSE RECOVERY CHARACTERISTICS (TYPICAL)



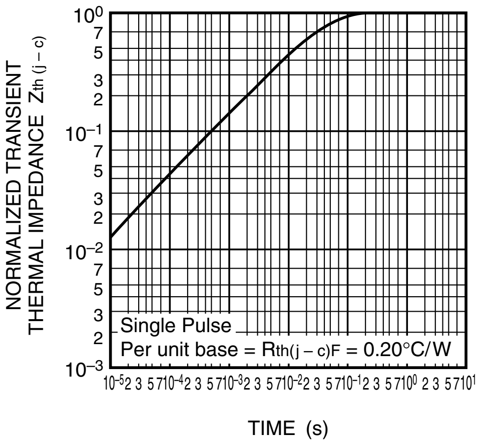
ID VS. fc CHARACTERISTICS (TYPICAL)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (IGBT PART)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (FWDi PART)



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